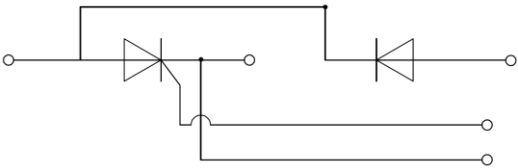




°C		



	°C			
				°C
				°C



	°C					
	°C					
	°C					
	°C					
	°C					
	°C					

FIG.1:Power dissipation vs. on-state current
(per thyristor or diode)

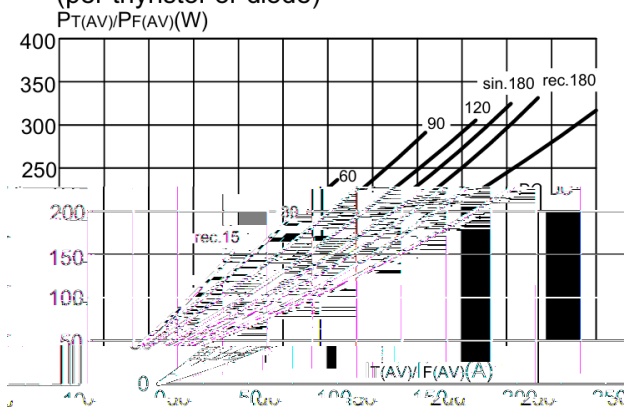


FIG.2: Maximum transient thermal impedance
junction to case(per thyristor or diode)

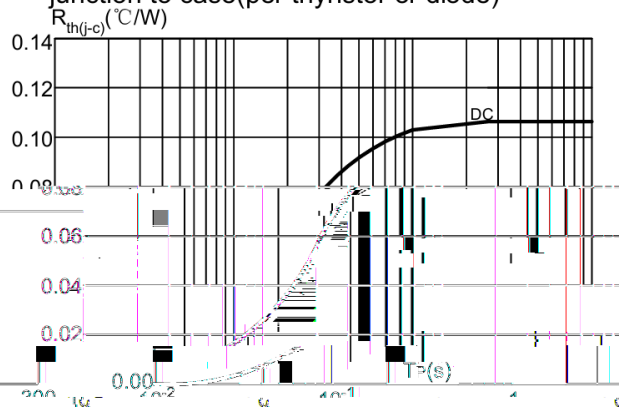


FIG.3:Forward characteristics
(per thyristor or diode)

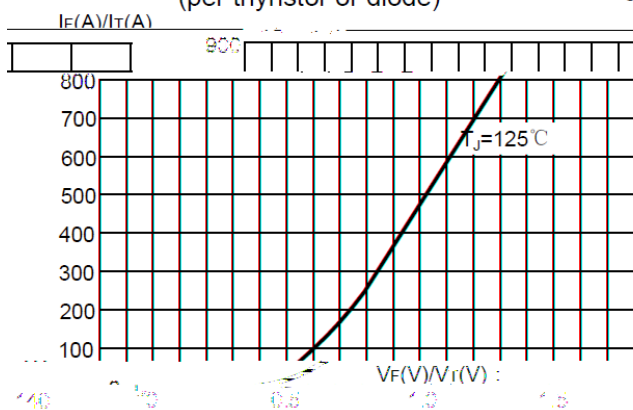


FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature

